

What is claimed is:

1. A semiconductor device comprising a support member, a semiconductor chip, a die-bonding material for attaching the semiconductor chip to the support member, and a resin encapsulant member for encapsulating the semiconductor chip, wherein;

5 said die-bonding material is a film containing an organic matter; said film having a water absorption of 1.5% by volume or less.

2. (CANCELED) A semiconductor device comprising a support member, a semiconductor chip, a die-bonding material for attaching the semiconductor chip to the support member, and a resin encapsulant member
10 for encapsulating the semiconductor chip, wherein;

 said die-bonding material is a film containing an organic matter; said film having a saturation moisture absorption of 1.0% by volume or less.

3. A semiconductor device comprising a support member, a semiconductor chip, a die-bonding material for attaching the semiconductor
15 chip to the support member, and a resin encapsulant member for encapsulating the semiconductor chip, wherein;

 said die-bonding material is a film containing an organic matter; said film having a residual volatile component in an amount not more than 3.0% by weight.

20 4. A semiconductor device comprising a support member, a semiconductor chip, a die-bonding material for attaching the semiconductor chip to the support member, and a resin encapsulant member for

encapsulating the semiconductor chip, wherein;

said die-bonding material is a film containing an organic matter; said film having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

5 5. A semiconductor device comprising a support member, a semiconductor chip, a die-bonding material for attaching the semiconductor chip to the support member, and a resin encapsulant member for encapsulating the semiconductor chip, wherein;

 said die-bonding material is a film containing an organic matter; said
10 film having, at the stage where the semiconductor chip has been bonded to the support member, a void volume of 10% or less in terms of voids present in the die-bonding material and at the interface between the die-bonding material and the support member.

 6. A semiconductor device comprising a support member, a
15 semiconductor chip, a die-bonding material for attaching the semiconductor chip to the support member, and a resin encapsulant member for encapsulating the semiconductor chip, wherein;

 said die-bonding material is a film containing an organic matter; said
film having a peel strength of 0.5 Kgf/5 × 5 mm chip or above at the stage
20 where the semiconductor chip has been bonded to the support member.

 7. A semiconductor device comprising a support member, a semiconductor chip, a die-bonding material for attaching the semiconductor chip to the support member, and a resin encapsulant member for

encapsulating the semiconductor chip, wherein;

said die-bonding material is a film containing an organic matter; said film i) having a planar dimension not larger than the planar dimension of the semiconductor chip, and ii) not protruding outward from the region of the semiconductor chip at the stage where the semiconductor chip has been bonded to the support member.

8. A process for fabricating a semiconductor device, comprising the steps of attaching a semiconductor chip to a support member, and encapsulating the semiconductor chip with a resin;

said attaching being carried out with a filmy die-bonding material containing an organic matter; said filmy die-bonding material having a water absorption of 1.5% by volume or less.

9. (CANCELED) A process for fabricating a semiconductor device, comprising the steps of attaching a semiconductor chip to a support member, and encapsulating the semiconductor chip with a resin;

said attaching being carried out with a filmy die-bonding material containing an organic matter; said filmy die-bonding material having a saturation moisture absorption of 1.0% by volume or less.

10. A process for fabricating a semiconductor device, comprising the steps of attaching a semiconductor chip to a support member, and encapsulating the semiconductor chip with a resin;

said attaching being carried out with a filmy die-bonding material containing an organic matter; said filmy die-bonding material having a residual

volatile component in an amount not more than 3.0% by weight.

11. A process for fabricating a semiconductor device, comprising the steps of attaching a semiconductor chip to a support member, and encapsulating the semiconductor chip with a resin;

5 said attaching being carried out with a filmy die-bonding material containing an organic matter; said filmy die-bonding material having a modulus of elasticity of 10 MPa or less at a temperature of 250 °C.

12. A process for fabricating a semiconductor device, comprising the steps of attaching a semiconductor chip to a support member, and
10 encapsulating the semiconductor chip with a resin;

 said attaching being carried out with a filmy die-bonding material containing an organic matter; said filmy die-bonding material having, at the stage where the semiconductor chip has been bonded to the support member, a void volume of 10% or less in terms of voids present in the die-bonding material and at the interface between the die-bonding material and
15 the support member.

13. A process for fabricating a semiconductor device, comprising the steps of attaching a semiconductor chip to a support member, and encapsulating the semiconductor chip with a resin;

20 said attaching being carried out with die-bonding material comprising a filmy die-bonding material containing an organic matter; said filmy die-bonding material having a peel strength of 0.5 kgf/5 × 5 mm chip or above at the stage where the semiconductor chip has been bonded to the support member.

14. A process for fabricating a semiconductor device, comprising the steps of attaching a semiconductor chip to a support member, and encapsulating the semiconductor chip with a resin;

5 said attaching being carried out with a filmy die-bonding material containing an organic matter; said filmy die-bonding material i) having a planar dimension not larger than the planar dimension of the semiconductor chip, and ii) not protruding outward from the region of the semiconductor chip at the stage where the semiconductor chip has been bonded to the support member.

10 15. A process for fabricating a semiconductor device, comprising the steps of attaching a semiconductor chip to a support member, and encapsulating the semiconductor chip with a resin;

 said attaching being carried out with a filmy die-bonding material containing an organic matter;

15 the process further comprising the steps of mounting said semiconductor chip on said filmy die-bonding material; and

 attaching said semiconductor chip to said filmy die-bonding material under conditions of a temperature of 150°C to 250°C, bonding time of 0.1
20 (inclusive) second to 2 seconds, and a pressure of 0.1 to 4 gf/mm².

16. A process for fabricating a semiconductor device, according to any one of claims 8 to 13 and 14, further comprising the steps of mounting said semiconductor chip on said filmy die-bonding material;

and

attaching said semiconductor chip to said filmy die-bonding material under conditions of a temperature of 150°C to 250°C, bonding time of 0.1 (inclusive) second to 2 seconds, and a pressure of 0.1 to 4 gf/mm².

5 17. The semiconductor device as described in Claim 3 wherein said die-bonding material is a film containing an organic matter; said film having a saturation moisture absorption of 1.0% by volume or less.

10 18. A semiconductor device as described in Claim 6 wherein said die-bonding material is a film containing an organic matter; said film having a saturation moisture absorption of 1.0% by volume or less.

 19. The process for fabricating a semiconductor device as described in Claim 10 wherein said filmy die-bonding material has a saturation moisture absorption of 1.0% by volume or less.

15 20. The process for fabricating a semiconductor device as described in Claim 12 wherein said filmy die-bonding material has a saturation moisture absorption of 1.0% by volume or less.

 21. A die-bonding material for use in a process for fabricating a semiconductor device, comprising the steps of attaching a semiconductor chip to a support member and encapsulating the semiconductor chip with a resin;
20 said die-bonding material being a film containing an organic matter; said film having a water absorption of 1.5% by volume or less.

22. A die-bonding material for use in a process for fabricating a semiconductor device, comprising the steps of attaching a semiconductor chip to a support member, and encapsulating the semiconductor chip with a resin;

said die-bonding material being a film containing an organic matter;

5 said film having a residual volatile component in an amount not more than 3.0% by weight.

23. The die-bonding material as described in Claim 22 wherein said film has a saturation moisture absorption of 1.0% by volume or less.

24. A die-bonding material for use in a process for fabricating a semiconductor device, comprising the steps of attaching a semiconductor chip to a support member, and encapsulating the semiconductor chip with a resin;

10 said die-bonding material being a film containing an organic matter; said film having a modulus of elasticity of 10 Mpa or less at a temperature of 250 °C.